Application No.: 10/611,892 Docket No.: M4065.0646/P646

AMENDMENTS TO THE SPECIFICATION

Replace the title of the invention at the title page and at the beginning of the specification at page 2 with the following:

OPTIMIZED ASYMMETRICAL TRANSISTOR FOR IMAGER DEVICE

Replace paragraph 0012 with the following:

[0012] FIGs. 2(a) and 2(b) show[[s]] alternative circuits as in FIGs. 1(a), 1(b), or 1(c), where the various FIG. 1 alternative cross-sections are shown through line 1-1'; FIG. 2(a) shows an alternative embodiment to that shown in FIG. 2.

Replace paragraph 0031 with the following:

[0031] FIG. 2(a) shows the same a pixel 10 circuit (as shown in FIG. 1(a), 1(b), and 1(c)) from above. The pixel 10 of FIG. 2(a) shows a one-sided active area extension region 40 at the transfer transistor 15 and two-sided active area extension regions 40 at the other transistors 14, 16, and 18, of the pixel 10. FIG. 2(a) also shows how the gate length 44 of the transfer transistor 15 can be greater relative to the gate lengths 44' of the other transistors of the pixel 10 in accordance with an embodiment of the invention, as further discussed below with reference to FIGs. 1(a), 1(b), and 1(c). FIG. 2(b) shows an alternative embodiment of the pixel 10 where not only the transfer transistor 15 has a one-sided active area extension region 40, but so do the reset transistor 14 and the source follower transistor 16.